

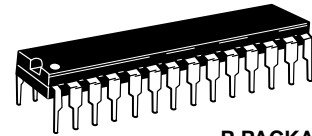
64K x 4 Bit Fast Static RAM With Output Enable

The MCM6209C is fabricated using Motorola's high-performance silicon-gate CMOS technology. Static design eliminates the need for external clocks or timing strobes, while CMOS circuitry reduces power consumption and provides for greater reliability.

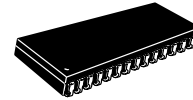
This device meets JEDEC standards for functionality and pinout, and is available in plastic dual-in-line and plastic small-outline J-leaded packages.

- Single 5 V ± 10% Power Supply
- Fully Static — No Clock or Timing Strokes Necessary
- Fast Access Times: 12, 15, 20, 25, and 35 ns
- Equal Address and Chip Enable Access Times
- Output Enable (\bar{G}) Feature for Increased System Flexibility and to Eliminate Bus Contention Problems
- Low Power Operation: 135 – 165 mA Maximum AC
- Fully TTL Compatible — Three-State Output

MCM6209C

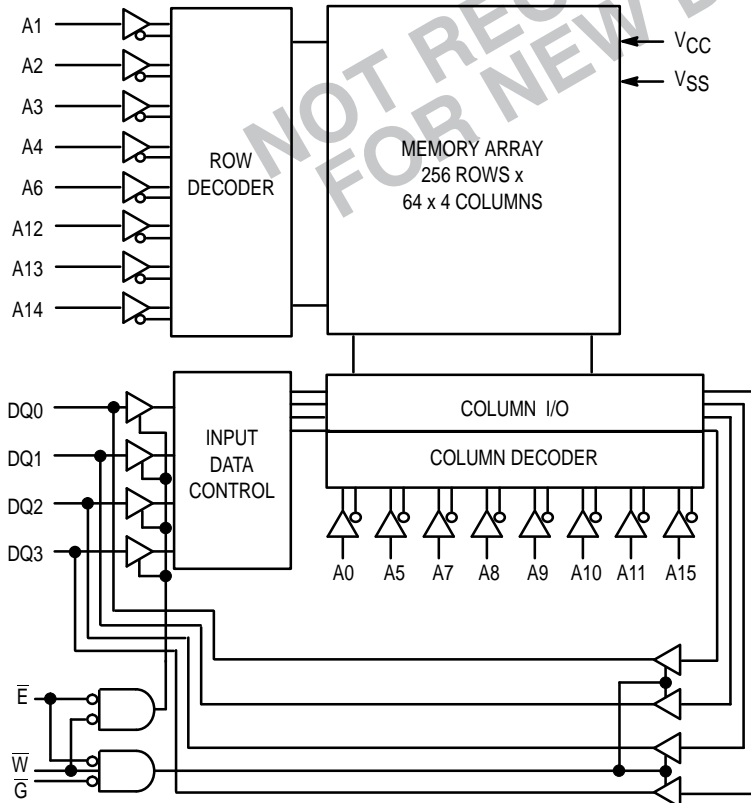


P PACKAGE
300 MIL PLASTIC
CASE 710B-01



J PACKAGE
300 MIL SOJ
CASE 810B-03

BLOCK DIAGRAM



PIN ASSIGNMENT

| | | | |
|-----------|----|----|-----------|
| NC | 1 | 28 | VCC |
| A0 | 2 | 27 | A15 |
| A1 | 3 | 26 | A14 |
| A2 | 4 | 25 | A13 |
| A3 | 5 | 24 | A12 |
| A4 | 6 | 23 | A11 |
| A5 | 7 | 22 | A10 |
| A6 | 8 | 21 | NC |
| A7 | 9 | 20 | NC |
| A8 | 10 | 19 | DQ0 |
| A9 | 11 | 18 | DQ1 |
| E | 12 | 17 | DQ2 |
| \bar{G} | 13 | 16 | DQ3 |
| VSS | 14 | 15 | \bar{W} |

PIN NAMES

| | |
|-----------|------------------------|
| A0 – A15 | Address Input |
| DQ0 – DQ3 | Data Input/Data Output |
| \bar{W} | Write Enable |
| \bar{G} | Output Enable |
| \bar{E} | Chip Enable |
| NC | No Connection |
| VCC | Power Supply (+ 5 V) |
| VSS | Ground |

TRUTH TABLE (X = Don't Care)

| \bar{E} | \bar{G} | \bar{W} | Mode | V _{CC} Current | Output | Cycle |
|-----------|-----------|-----------|-----------------|-------------------------------------|------------------|-------|
| H | X | X | Not Selected | I _{SB1} , I _{SB2} | High-Z | — |
| L | H | H | Output Disabled | I _{CCA} | High-Z | — |
| L | L | H | Read | I _{CCA} | D _{out} | Read |
| L | X | L | Write | I _{CCA} | High-Z | Write |

ABSOLUTE MAXIMUM RATINGS (See Note)

| Rating | Symbol | Value | Unit |
|--|------------------------------------|--------------------------------|------|
| Power Supply Voltage | V _{CC} | - 0.5 to + 7.0 | V |
| Voltage Relative to V _{SS} For Any Pin Except V _{CC} | V _{in} , V _{out} | - 0.5 to V _{CC} + 0.5 | V |
| Output Current | I _{out} | ± 20 | mA |
| Power Dissipation | P _D | 1.0 | W |
| Temperature Under Bias | T _{bias} | - 10 to + 85 | °C |
| Operating Temperature | T _A | 0 to + 70 | °C |
| Storage Temperature — Plastic | T _{stg} | - 55 to + 125 | °C |

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPERATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.

This CMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow of at least 500 linear feet per minute is maintained.

DC OPERATING CONDITIONS AND CHARACTERISTICS

(V_{CC} = 5.0 V ± 10%, T_A = 0 to 70°C, Unless Otherwise Noted)

RECOMMENDED OPERATING CONDITIONS

| Parameter | Symbol | Min | Typ | Max | Unit |
|--|-----------------|--------|-----|-------------------------|------|
| Supply Voltage (Operating Voltage Range) | V _{CC} | 4.5 | 5.0 | 5.5 | V |
| Input High Voltage | V _{IH} | 2.2 | — | V _{CC} + 0.3** | V |
| Input Low Voltage | V _{IL} | - 0.5* | — | 0.8 | V |

* V_{IL} (min) = - 0.5 V dc; V_{IL} (min) = - 2.0 V ac (pulse width ≤ 20 ns)

** V_{IH} (max) = V_{CC} + 0.3 V dc; V_{IH} (max) = V_{CC} + 2.0 V ac (pulse width ≤ 20 ns)

DC CHARACTERISTICS

| Parameter | Symbol | Min | Max | Unit |
|--|---------------------|-----|-----|------|
| Input Leakage Current (All Inputs, V _{in} = 0 to V _{CC}) | I _{lkg(I)} | — | ± 1 | μA |
| Output Leakage Current ($\bar{E} = V_{IH}$ or $\bar{G} = V_{IH}$, V _{out} = 0 to V _{CC}) | I _{lkg(O)} | — | ± 1 | μA |
| Standby Current ($\bar{E} \geq V_{CC} - 0.2 V^*$, V _{in} ≤ V _{SS} + 0.2 V, or ≥ V _{CC} - 0.2 V, V _{CC} = Max, f = 0 MHz) | I _{SB2} | — | 20 | mA |
| Output Low Voltage (I _{OL} = 8.0 mA) | V _{OL} | — | 0.4 | V |
| Output High Voltage (I _{OH} = - 4.0 mA) | V _{OH} | 2.4 | — | V |

*For devices with multiple chip enables, $\bar{E}1$ and $\bar{E}2$ are represented by \bar{E} in this data sheet. $\bar{E}2$ is of opposite polarity to \bar{E} .

POWER SUPPLY CURRENTS

| Parameter | Symbol | - 12 | - 15 | - 20 | - 25 | - 35 | Unit |
|---|------------------|------|------|------|------|------|------|
| AC Supply Current (I _{out} = 0 mA, V _{CC} = Max, f = f _{max}) | I _{CCA} | 165 | 155 | 145 | 135 | 130 | mA |
| Standby Current ($\bar{E} = V_{IH}$, V _{CC} = Max, f = f _{max}) | I _{SB1} | 55 | 50 | 45 | 40 | 35 | mA |

CAPACITANCE (f = 1 MHz, dV = 3 V, T_A = 25°C, Periodically Sampled Rather Than 100% Tested)

| Characteristic | Symbol | Max | Unit |
|--|------------------|-----|------|
| Address Input Capacitance | C _{in} | 6 | pF |
| Control Pin Input Capacitance (\overline{E} , \overline{G} , \overline{W}) | C _{in} | 6 | pF |
| I/O Capacitance | C _{I/O} | 8 | pF |

AC OPERATING CONDITIONS AND CHARACTERISTICS

(V_{CC} = 5.0 V ± 10%, T_A = 0 to +70°C, Unless Otherwise Noted)

Input Timing Measurement Reference Level 1.5 V Output Timing Measurement Reference Level 1.5 V
 Input Pulse Levels 0 to 3.0 V Output Load Figure 1A Unless Otherwise Noted
 Input Rise/Fall Time 5 ns

READ CYCLE (See Notes 1 and 2)

| Parameter | Symbol | - 12 | | - 15 | | - 20 | | - 25 | | - 35 | | Unit | Notes |
|-------------------------------------|---------------------|------|-----|------|-----|------|-----|------|-----|------|-----|------|---------|
| | | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max | | |
| Read Cycle Time | t _{AVAV} | 12 | — | 15 | — | 20 | — | 25 | — | 35 | — | ns | 2 |
| Address Access Time | t _{AVQV} | — | 12 | — | 15 | — | 20 | — | 25 | — | 35 | ns | |
| Enable Access Time | t _{ELQV} | — | 12 | — | 15 | — | 20 | — | 25 | — | 35 | ns | 3 |
| Output Enable Access Time | t _{GLQV} | — | 6 | — | 8 | — | 10 | — | 12 | — | 15 | ns | |
| Output Hold from Address Change | t _{AXQX} | 4 | — | 4 | — | 4 | — | 4 | — | 4 | — | ns | |
| Enable Low to Output Active | t _{ELQX} | 4 | — | 4 | — | 4 | — | 4 | — | 4 | — | ns | 4, 5, 6 |
| Enable High to Output High-Z | t _{EHQZ} | 0 | 6 | 0 | 8 | 0 | 9 | 0 | 10 | 0 | 10 | ns | 4, 5, 6 |
| Output Enable Low to Output Active | t _{GLQX} | 0 | — | 0 | — | 0 | — | 0 | — | 0 | — | ns | 4, 5, 6 |
| Output Enable High to Output High-Z | t _{GHQZ} | 0 | 6 | 0 | 7 | 0 | 8 | 0 | 10 | 0 | — | ns | 4, 5, 6 |
| Power Up Time | t _{ELICCH} | 0 | — | 0 | — | 0 | — | 0 | — | 0 | — | ns | |
| Power Down Time | t _{EHICCL} | — | 12 | — | 15 | — | 20 | — | 25 | — | 35 | ns | |

NOTES:

1. \overline{W} is high for read cycle.
2. All timings are referenced from the last valid address to the first transitioning address.
3. Addresses valid prior to or coincident with \overline{E} going low.
4. At any given voltage and temperature, t_{EHQZ} max is less than t_{ELQX} min, and t_{GHQZ} max is less than t_{GLQX} min, both for a given device and from device to device.
5. Transition is measured ± 500 mV from steady-state voltage with load of Figure 1B.
6. This parameter is sampled and not 100% tested.
7. Device is continuously selected ($\overline{E} = V_{IL}$, $\overline{G} \leq V_{IL}$).

AC TEST LOADS

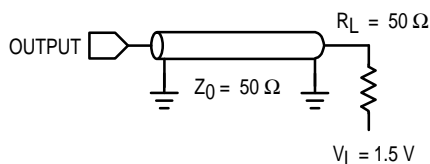


Figure 1A

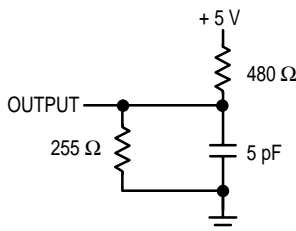
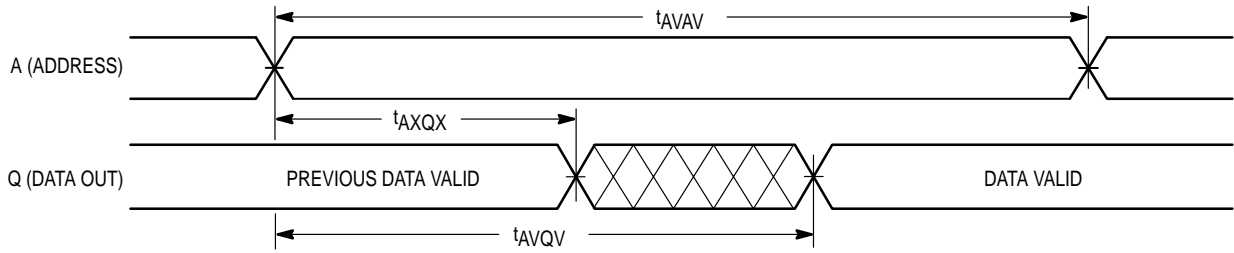


Figure 1B

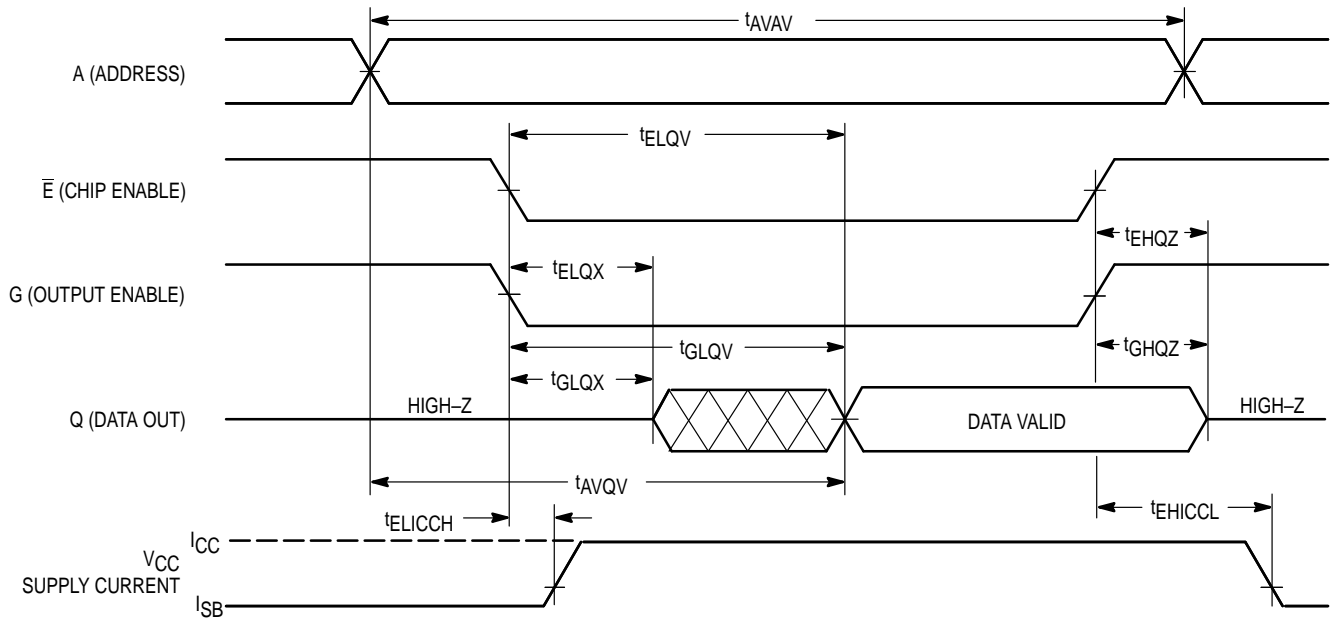
TIMING LIMITS

The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. Thus, address setup time is shown as a minimum since the system must supply at least that much time (even though most devices do not require it). On the other hand, responses from the memory are specified from the device point of view. Thus, the access time is shown as a maximum since the device never provides data later than that time.

READ CYCLE 1 (See Note 8)



READ CYCLE 2 (See Notes 2 and 4)



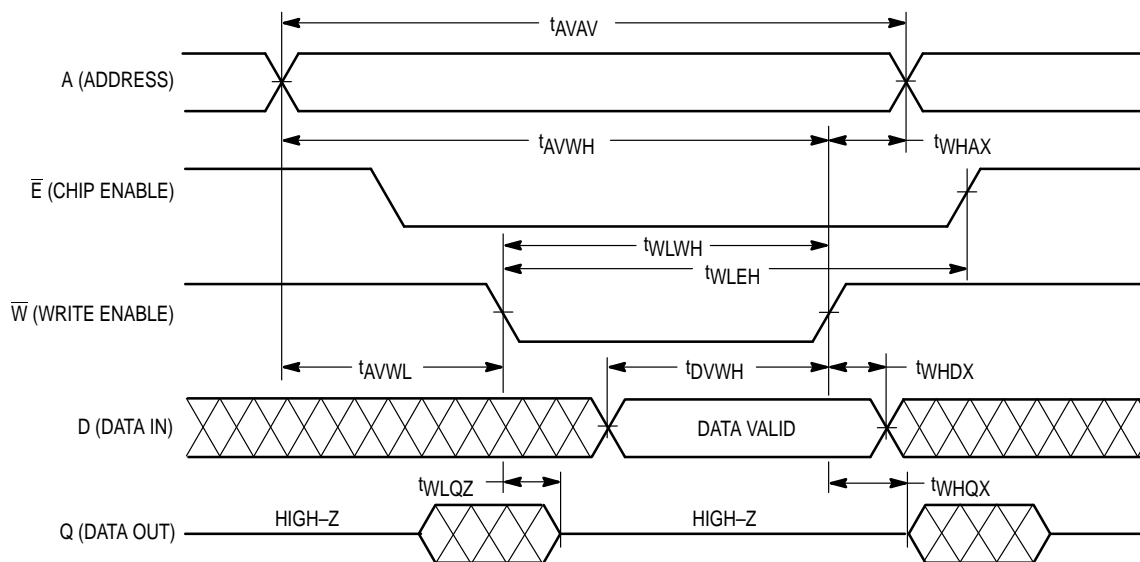
WRITE CYCLE 1 (\overline{W} Controlled, See Notes 1, 2, and 3)

| Parameter | Symbol | - 12 | | - 15 | | - 20 | | - 25 | | - 35 | | Unit | Notes |
|--|----------------------------|------|-----|------|-----|------|-----|------|-----|------|-----|------|---------|
| | | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max | | |
| Write Cycle Time | t_{AVAV} | 12 | — | 15 | — | 20 | — | 25 | — | 35 | — | ns | 3 |
| Address Setup Time | t_{AVWL} | 0 | — | 0 | — | 0 | — | 0 | — | 0 | — | ns | |
| Address Valid to End of Write | t_{AVWH} | 10 | — | 12 | — | 15 | — | 20 | — | 20 | — | ns | |
| Write Pulse Width | t_{WLWH} , t_{WLEH} | 10 | — | 12 | — | 15 | — | 20 | — | 20 | — | ns | |
| Write Pulse Width, \overline{G} High | t_{WLWH} , t_{WLEH} | 8 | — | 10 | — | 12 | — | 15 | — | 15 | — | ns | 4 |
| Data Valid to End of Write | t_{DVWH} | 6 | — | 7 | — | 8 | — | 10 | — | 10 | — | ns | |
| Data Hold Time | t_{WHDX} | 0 | — | 0 | — | 0 | — | 0 | — | 0 | — | ns | |
| Write Low to Output High-Z | t_{WLQZ} | 0 | 6 | 0 | 7 | 0 | 8 | 0 | 10 | 0 | 10 | ns | 5, 6, 7 |
| Write High to Output Active | t_{WHQX} | 4 | — | 4 | — | 4 | — | 4 | — | 4 | — | ns | 5, 6, 7 |
| Write Recovery Time | t_{WHAX} | 0 | — | 0 | — | 0 | — | 0 | — | 0 | — | ns | |

NOTES:

1. A write occurs during the overlap of \overline{E} low and \overline{W} low.
2. For Output Enable devices, if \overline{G} goes low coincident with or after \overline{W} goes low, the output will remain in a high impedance state.
3. All timings are referenced from the last valid address to the first transitioning address.
4. For Output Enable devices, if $\overline{G} \geq V_{IH}$, the output will remain in a high impedance state.
5. At any given voltage and temperature, t_{WLQZ} max is less than t_{WHQX} min, both for a given device and from device to device.
6. Transition is measured ± 500 mV from steady-state voltage with load of Figure 1B.
7. This parameter is sampled and not 100% tested.

WRITE CYCLE 1 (\overline{W} Controlled, See Note 2)



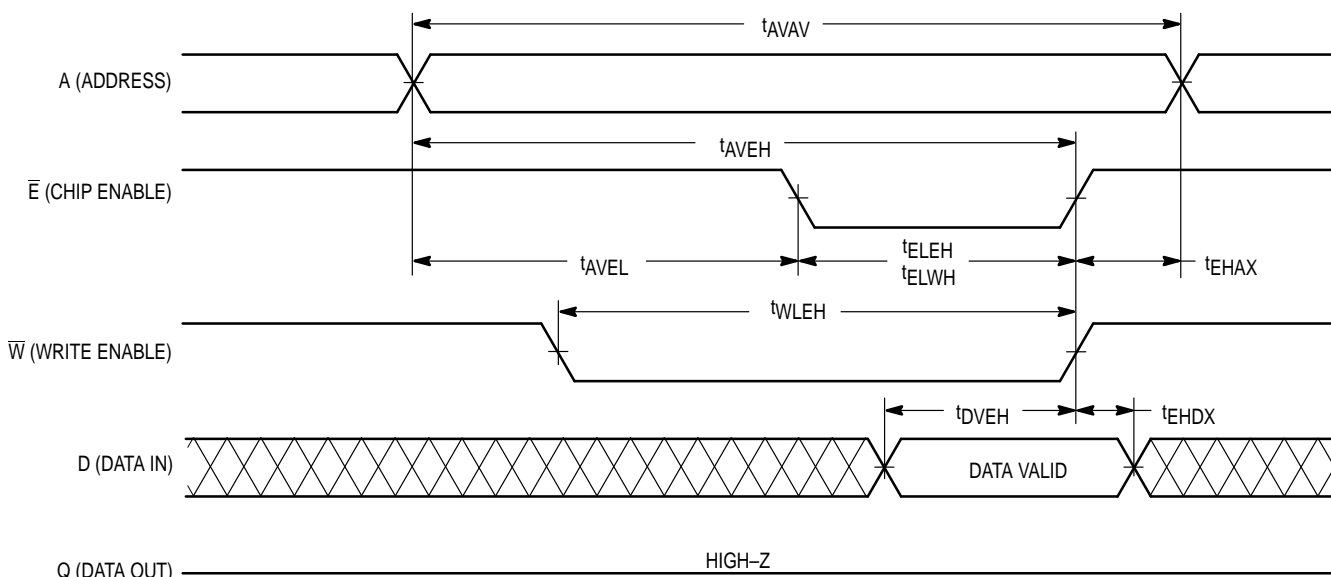
WRITE CYCLE 2 (\bar{E} Controlled, See Notes 1, 2, and 3)

| Parameter | Symbol | - 12 | | - 15 | | - 20 | | - 25 | | - 35 | | Unit | Notes |
|-------------------------------|----------------------------|------|-----|------|-----|------|-----|------|-----|------|-----|------|-------|
| | | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max | | |
| Write Cycle Time | t_{AVAV} | 12 | — | 15 | — | 20 | — | 25 | — | 35 | — | ns | 3 |
| Address Setup Time | t_{AVEL} | 0 | — | 0 | — | 0 | — | 0 | — | 0 | — | ns | |
| Address Valid to End of Write | t_{AVEH} | 10 | — | 12 | — | 15 | — | 20 | — | 20 | — | ns | |
| Enable to End of Write | t_{ELEH} , t_{ELWH} | 8 | — | 10 | — | 12 | — | 15 | — | 15 | — | ns | 4, 5 |
| Data Valid to End of Write | t_{DVEH} | 6 | — | 7 | — | 8 | — | 10 | — | 10 | — | ns | |
| Data Hold Time | t_{EHDX} | 0 | — | 0 | — | 0 | — | 0 | — | 0 | — | ns | |
| Write Recovery Time | t_{EHAX} | 0 | — | 0 | — | 0 | — | 0 | — | 0 | — | ns | |

NOTES:

1. A write occurs during the overlap of \bar{E} low and \bar{W} low.
2. For Output Enable devices, if \bar{G} goes low coincident with or after \bar{W} goes low, the output will remain in a high impedance state.
3. All timings are referenced from the last valid address to the first transitioning address.
4. If \bar{E} goes low coincident with or after \bar{W} goes low, the output will remain in a high impedance state.
5. If \bar{E} goes high coincident with or before \bar{W} goes high, the output will remain in a high impedance state.

WRITE CYCLE 2 (\bar{E} Controlled, See Note 2)



ORDERING INFORMATION

(Order by Full Part Number)

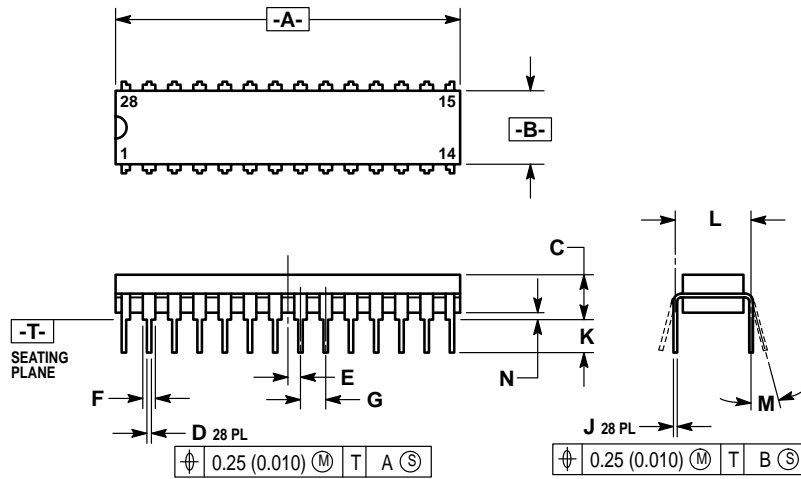
MCM 6209C X XX XX

Motorola Memory Prefix — **MCM**
 Part Number — **6209C**
 Shipping Method (R2 = Tape and Reel, Blank = Rails)
 Speed (15 = 15 ns, 20 = 20 ns, 25 = 25 ns, 35 = 35 ns)
 Package (P = Plastic DIP, J = Plastic SOJ)

Full Part Numbers — MCM6209CP15 MCM6209CJ15 MCM6209CJ15R2
 MCM6209CP20 MCM6209CJ20 MCM6209CJ20R2
 MCM6209CP25 MCM6209CJ25 MCM6209CJ25R2
 MCM6209CP35 MCM6209CJ35 MCM6209CJ35R2

PACKAGE DIMENSIONS

P PACKAGE 300 MIL PLASTIC CASE 710B-01

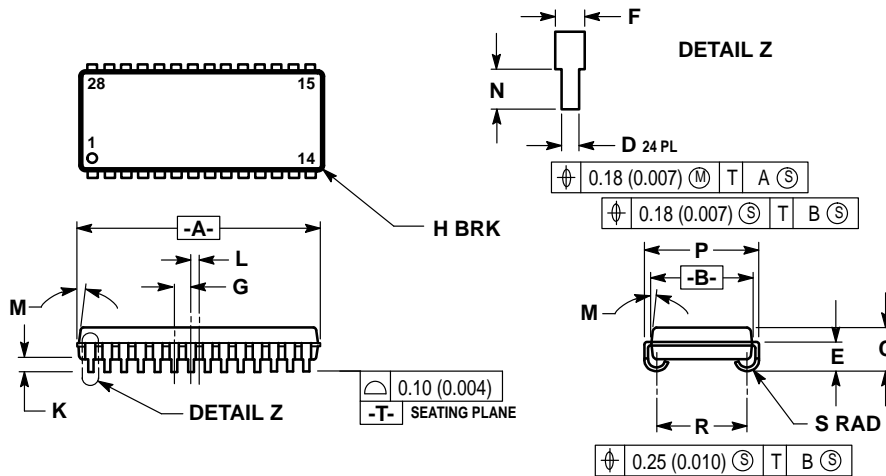


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIMENSION A AND B DOES NOT INCLUDE MOLD FLASH. MAXIMUM MOLD FLASH 0.25 (0.010).

| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|-------|-----------|-------|
| | MIN | MAX | MIN | MAX |
| A | 34.55 | 34.79 | 1.360 | 1.370 |
| B | 7.12 | 7.62 | 0.280 | 0.300 |
| C | 3.81 | 4.57 | 0.150 | 0.180 |
| D | 0.39 | 0.53 | 0.015 | 0.021 |
| E | 1.27 BSC | | 0.050 BSC | |
| F | 1.15 | 1.39 | 0.045 | 0.055 |
| G | 2.54 BSC | | 0.100 BSC | |
| J | 0.21 | 0.30 | 0.008 | 0.012 |
| K | 3.18 | 3.42 | 0.125 | 0.135 |
| L | 7.62 BSC | | 0.300 BSC | |
| M | 0° | 15° | 0° | 15° |
| N | 0.51 | 1.01 | 0.020 | 0.040 |


J PACKAGE 300 MIL SOJ CASE 810B-03



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. DIMENSION A & B DO NOT INCLUDE MOLD PROTRUSION. MOLD PROTRUSION SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
3. CONTROLLING DIMENSION: INCH.
4. DIM R TO BE DETERMINED AT DATUM -T-.
5. 810B-01 AND -02 OBSOLETE. NEW STANDARD 810B-03.

| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|-------|-----------|-------|
| | MIN | MAX | MIN | MAX |
| A | 18.29 | 18.54 | 0.720 | 0.730 |
| B | 7.50 | 7.74 | 0.295 | 0.305 |
| C | 3.26 | 3.75 | 0.128 | 0.148 |
| D | 0.39 | 0.50 | 0.015 | 0.020 |
| E | 2.24 | 2.48 | 0.088 | 0.098 |
| F | 0.67 | 0.81 | 0.026 | 0.032 |
| G | 1.27 BSC | | 0.050 BSC | |
| H | — | 0.50 | — | 0.020 |
| K | 0.89 | 1.14 | 0.035 | 0.045 |
| L | 0.64 BSC | | 0.025 BSC | |
| M | 0° | 10° | 0° | 10° |
| N | 0.76 | 1.14 | 0.030 | 0.045 |
| P | 8.38 | 8.64 | 0.330 | 0.340 |
| R | 6.60 | 6.86 | 0.260 | 0.270 |
| S | 0.77 | 1.01 | 0.030 | 0.040 |

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